

L Number	Hits	Search Text	DB	Time stamp
1	1	("6580152").PN.	USPAT	2003/09/04 12:51
2	5265	((isolation and substrate) near (trench or region or island))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 12:56
3	4776	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 12:57
4	3156	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)) and ((semiconductor or silicon) and (Sin or nitride) and (oxide or sio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 13:00
5	2893	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)) and ((semiconductor or silicon) and (Sin or nitride) and (oxide or sio))) and ((semiconductor or silicon) near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 13:00
6	2478	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)) and ((semiconductor or silicon) and (Sin or nitride) and (oxide or sio))) and ((semiconductor or silicon) near substrate)) and ((Sin or nitride) with (oxide or sio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 13:00
7	2478	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)) and ((semiconductor or silicon) and (Sin or nitride) and (oxide or sio))) and ((semiconductor or silicon) near substrate)) and ((Sin or nitride) with (oxide or sio))) and ((oxide or sio) with (oxide or sio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 13:01
8	99	((isolation and substrate) near (trench or region or island))) and (@ad<20020115)) and ((semiconductor or silicon) and (Sin or nitride) and (oxide or sio))) and ((semiconductor or silicon) near substrate)) and ((Sin or nitride) with (oxide or sio))) and ((oxide or sio) near (oxide or sio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/04 13:01